

Press Fit Diode, 50A

Features

- Low Leakage
- Low Forward Voltage Drop
- Low Cost
- High Surge Current Capability

Mechanical Characteristics

- **Chip:** Gpp Chip
- **Encapsulation:** Epoxy Sealed
- **Lead:** Plated Lead, Solderable
- **Mounting:** Press Fit
- **Weight:** 6.5 grams (approx.)

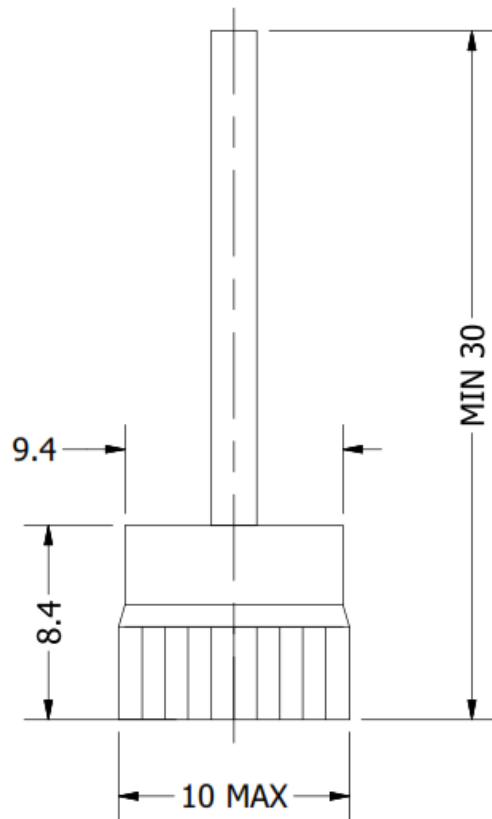


PRESS-FIT DIODE

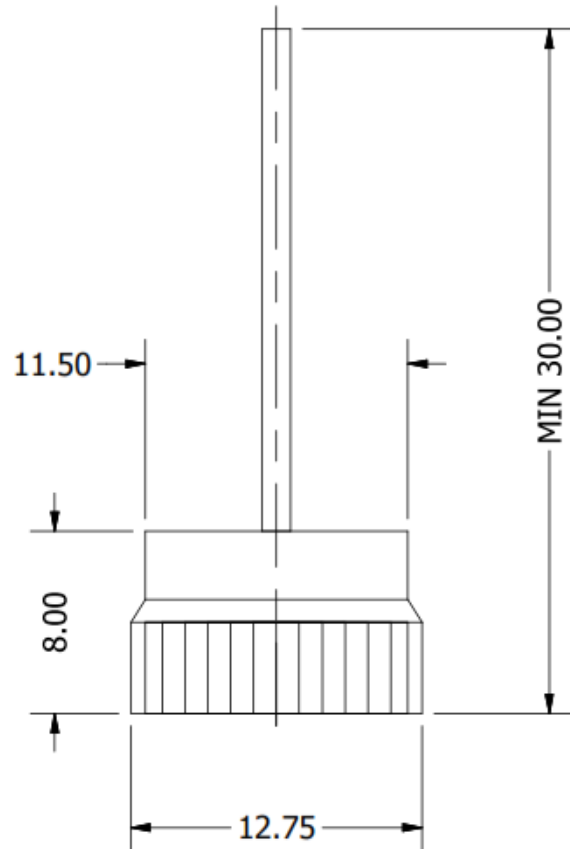
Electrical Characteristics (T _A = 25 ^o C unless otherwise specified)						
Parameter		Symbol	NP5002(R)	NP5004(R)	NP5006(R)	Units
Maximum repetitive peak reverse voltage		V _{RRM}	200	400	600	V
Maximum RMS Voltage		V _{RMS}	140	280	420	V
Maximum DC Blocking Voltage		V _{DC}	200	400	600	V
Maximum average forward output current @ T _A = 105 ^o C		I _{F(AV)}	50			A
Peak forward surge current (8.3ms) single half sine-wave superimposed on rated load		I _{FSM}	600			A
Maximum instantaneous forward voltage drop @ 100 A		V _F	1.1			V
Maximum DC reverse current at rated DC blocking voltage	T _A = 25 ^o C	I _R	5.0			μA
	T _A = 100 ^o C		450			
Typical Thermal Resistance		R _{θ(j-c)}	0.8			°C/W
Operating and storage temperature		T _J , T _{STG}	-65 to +175			°C

Package Outline

(All dimensions in mm)



PACKAGE A



PACKAGE B

Ordering Table

NP	50	02	R
1	2	3	4

1 – Press-fit Diode

2 – Current Rating = $I_F (AV)$

3 – Voltage, V_{RRM} (as per table)

4 – Polarity:

- > None = Normal (Cathode to Base) (**Red** Color Epoxy)
- > R = Reverse (Anode to Base) (**Black** Color Epoxy)